





New Dosimeter Equipment

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A Radiation Monitoring System for CMS: why? how?
RadFETs and neutron diodes: operating principle
Test beam results
Conclusions







The Radiation Monitoring System for CMS

CMS radiation environment: mixed radiation field (IEL, NIEL)

Purpose of the system

- 1) Mapping of dose and fluence in each sub-detector: independent measurement of dose and fluence to cross-check for calibration, etc.
- 2) Studies of machine related backgrounds
- 3) Measurement of activation levels: planning of shutdown activities

Main characteristics of the system

- 1) Real-time online dosimetry: no need to access the experiment first
- 2) Separation between Ionising Energy Loss (dose) and Non-Ioning Energy Loss (fluence)

Beam-abort system: to protect against beam-losses (not looked into it yet)







The dosimeters

All dosimeters selected are commercially available, but some R&D in collaboration with the producers may be required.

Dose measurements (IEL)

MOSFET transistors called RadFETs (Radiation sensitive MOSFETs) Producers: NMRC in Ireland REM in UK Thomson and Nielsen in Canada Possible R&D: change in gate oxide thickness

Fluence measurements (NIEL)

p⁺/n/n⁺ diodes called neutron diodes Producer: University of Wollongong in Australia Possible R&D: change in base width







The dosimeters: operating principle

RadFETs

p-channel MOSFET transistors with calibrated sensitivity to ionising radiation Electron-hole pair production in the gate oxide by charged particle Positive space charge creation at the interface by hole trapping Negative charge induced in the substrate Increase in drop of voltage, V_{th} , across the transistor when biased with a constant current

Neutron diodes

 $p^+/n/n^+$ diodes with calibrated sensitivity to non-ionising radiation Bulk damage created in the intrinsic region by neutrons and other particles (p, π , e, etc.) New traps creation Decrease in minority carrier lifetime

Change in voltage, V_F, across the diode when biased forward with a constant current











RadFETs









2000 / 2001 test-beam program

Irradiations

2000: 192 MeV π^{-} (PSI) up to 1 $\equiv 10^{14} \pi/\text{cm}^2$, 500 MeV e⁻ (LIL) up to 4-7 $\equiv 10^{14} \text{ e/cm}^2$ 23 GeV p (IRRAD1) up to 0.5 $\equiv 10^{14} \text{ p/cm}^2$, n (IRRAD2) up to 2.4 $\equiv 10^{14} \text{ n/cm}^2$, 3.6 GeV π^{-} (T11) up to 2 $\equiv 10^{10} \pi/\text{cm}^2$ 2001: 23 GeV p (IRRAD1) up to 1 $\equiv 10^{14} \text{ p/cm}^2$, n (IRRAD2) up to 0.6 $\equiv 10^{14} \text{ n/cm}^2$, TCC2

Measurement protocol

All terminals shorted during irradiation Readings taken with beam on and off Injection of constant current: 10 μA, 100 μA, 160 μA for RadFETs, 1 mA for neutron diodes Readout of voltage: 2-5 times at few second interval for RadFETs 1 time after 180 ms for neutron diodes









Diodes: typical response curve



BC, 7.12.01

Conclusions

- A CMS Radiation Monitoring System is under development:
 - real-time online readout
 - separation IEL/NIEL
- Technologies for such system are available:
 - RadFETs for IEL
 - Neutron diodes for NIEL
 - as proved in test-beams last and this year.
- First irradiation in TCC2 performed this year: the dosimeters worked well in such environment.

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